



# Product data sheet

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SOT - 23

3. COLLECTOR

TRANSISTOR (NPN)

FEATURES

- Epitaxial planar die construction
- Complementary PNP Type available(MMBT2907A-

MS)

MARKING :1P

#### MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage	75	V
V <sub>CEO</sub>	Collector-Emitter Voltage	40	V
V <sub>EBO</sub>	Emitter-Base Voltage	6	V
Ιc	Collector Current -Continuous	600	mA
Pc	Collector Dissipation	300	mW
R₀ja	Thermal Resistance, Junction to Ambient	417	°C/W
T <sub>J</sub> ,Tstg	Operation Junction and Storage Temperature Range	-55~+150	°C

#### ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Pa rameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = 10μΑ, I <sub>E</sub> =0	75			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub> *	I <sub>C</sub> = 10mA, I <sub>B</sub> =0	40			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =10μΑ, I <sub>C</sub> =0	6			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =60V, I <sub>E</sub> =0			0.01	μA
Collector cut-off current	I <sub>CEX</sub>	V <sub>CE</sub> =30V,V <sub>BE(off)</sub> =3V			0.01	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = 3V, I <sub>C</sub> =0			0.1	μA
	h <sub>FE(1)</sub> *	V <sub>CE</sub> =10V, I <sub>C</sub> = 150mA	100		300	
DC current gain	h <sub>FE(2)</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> = 0.1mA	40			
	h <sub>FE(3)</sub> *	V <sub>CE</sub> =10V, I <sub>C</sub> = 500mA	42			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub> *	$I_{C}$ =500 mA, $I_{B}$ = 50mA $I_{C}$ =150 mA, $I_{B}$ =15mA			1 0.3	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub> *	$I_{C}$ =500 mA, $I_{B}$ = 50mA $I_{C}$ =150 mA, $I_{B}$ =15mA			2.0 1.2	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =20V, I <sub>C</sub> = 20mA, f=100MHz	300			MHz
Delay time	t <sub>d</sub>	V <sub>CC</sub> =30V, V <sub>BE(off)</sub> =-0.5V			10	ns
Rise time	tr	I <sub>C</sub> =150mA , I <sub>B1</sub> = 15mA			25	ns
Storage time	ts	$V_{CC}$ =30V, I <sub>C</sub> =150mA I <sub>B1</sub> =-I <sub>B2</sub> =15mA			225	ns
Fall time	t <sub>f</sub>				60	ns

\*pulse test: Pulse Width ≤300µs, Duty Cycle≤ 2.0%.

#### CLASSIFICATION OF hFE(1)

RANK	L	н
RANGE	100 - 200	200 - 300

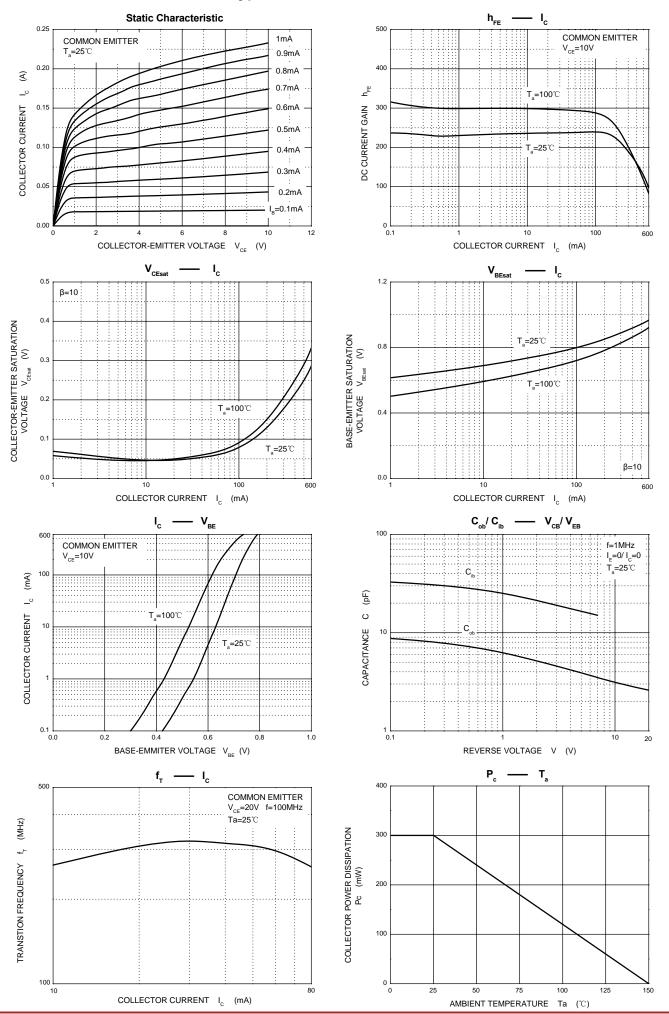


# MMBT2222A-MS HF 🐼

Semiconductor

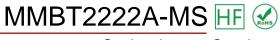
Compiance

#### **Typical Characteristics**



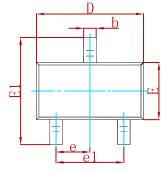
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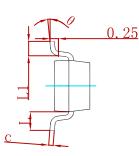


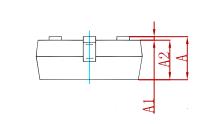


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## PACKAGE MECHANICAL DATA

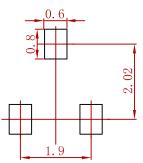






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
А	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950	)TYP	0.03	7 TYP	
e1	1.800	2.000	0.071	0.079	
L	0.550	) REF	0.022	2 REF	
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

## Suggested Pad Layout



Note:

Controlling dimension:in millimeters.
General tolerance:± 0.05mm.
The pad layout is for reference purposes only.

### **REEL SPECIFICATION**

P/N	PKG	QTY
MMBT2222A-MS	SOT-23	3000



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